

SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. §1.111
U.S. Appln. No. 10/695,802

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (previously presented): An island projection-modified part which has, on the substrate thereof, island projections having a width of from 5 to 300 μm and a height of from 2 to 200 μm and in which the island projections are roundish as a whole, and the number of the island projections is from 20 to 5,000/ mm^2 , wherein the island projections are formed of glass and they are spherical, partly spherical, semispherical, bell-shaped or mountain-shaped or are in the form of a mixture of two or more of these shapes

Claim 2 (canceled).

3. (original): The island projection-modified part as claimed in claim 1, wherein the island projections are formed on a glass-sprayed film that is formed on the substrate.

4. (currently amended): The island projection-modified part as claimed in claim 1~~2~~, wherein the glass to form the island projections is quartz glass.

5. (original): The island projection-modified part as claimed in claim 3, wherein the sprayed film is of quartz glass.

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6. (withdrawn): A method for producing the projection-modified part of claim 1, which comprises plasma-spraying a projection-forming material on the surface of a substrate or on the surface of a glass-sprayed film formed on a substrate to thereby form island projections thereon and in which the amount of the projection-forming material to be sprayed on the surface is from 1 to 20 mg/cm² of the area of that surface.

7. (original): A film-forming device that comprises the island projection-modified part of claim 1.

8. (original): A plasma-etching device wherein the island projection-modified part of claim 1 is used for the part on which a film may be deposited or etched through plasma etching.

9. (original): A plasma-cleaning device wherein the island projection-modified part of claim 1 is used for the part on which a film may be deposited or etched through back sputtering.

10. (currently amended): The island projection-modified part as claimed in claim 22, wherein the island projections are formed of ceramic and/or metal, and they are mountain-shaped and/or bell-shaped.

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11. (original): The island projection-modified part as claimed in claim 1, wherein the mean ratio of the height to the width (height/width) of the island projections falls between 0.3 and 1.5.

12. (original): The island projection-modified part as claimed in claim 10, wherein the surface of the substrate on which the island projections are formed has a surface roughness Ra of at most 5 μm .

13. (original): The island projection-modified part as claimed in claim 10, wherein the island projections are formed of materials having a different melting point and the material having a high melting point is enveloped in the other material having a low melting point to give the island projections.

14. (withdrawn): A method for producing the projection-modified part of claim 10, which comprises dashing a projection-forming material to the surface of a substrate while the material is in a semi-melted condition and in which the amount of the material to be applied to the surface is from 1 to 20 mg/cm^2 of the area of that surface.

15. (withdrawn): A method for producing the island projection-modified part of claim 10, which comprises preparing a spraying powder of particles of a high-melting-point material enveloped in a low-melting-point material and dashing it to a substrate in a mode of thermal

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spraying while the low-melting-point material is completely melted but the high-melting-point material is un-melted or semi-melted.

16. (withdrawn): The method as claimed in claim 14 for producing the island projection-modified part, wherein the substrate is, after thermally sprayed to have island projections formed thereon, further heated.

17. (withdrawn): The method as claimed in claim 15 for producing the island projection-modified part, wherein the substrate is, after thermally sprayed to have island projections formed thereon, further heated.

18. (original): A film-forming device wherein the part of claim 10 is used for the part that may receive a filmy deposit formed thereon through PVD or CVD.

19. (original): A plasma-etching device wherein the part of claim 10 is used for the part on which a film may be deposited or etched through plasma etching.

20. (original): A plasma-cleaning device wherein the part of claim 10 is used for the part on which a film may be deposited or etched through back sputtering.

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21. (currently amended): The island projection-modified part as claimed in claim 1, wherein at least some island projections do not overlap with each other, whereby a portion of the substrate is exposed and ~~it~~ separates at least some of the individual island projections.

22. (previously presented): An island projection-modified part which has, on the substrate thereof, island projections having a width of from 5 to 300 μm and a height of from 2 to 200 μm and in which the island projections are roundish as a whole and do not have any sharp edge, and the number of the island projections is from 20 to 5,000/ mm^2 .

23. (previously presented): The island projection-modified part as claimed in claim 22, wherein at least some island projections do not overlap with each other, whereby a portion of the substrate is exposed and separates at least some of the individual island projections.

24. (new): The island projection-modified part as claimed in claim 22, wherein the mean ratio of the height to the width (height/width) of the island projections falls between 0.3 and 1.5.